

Silicon PNP Power Transistors 2SA1306 2SA1306A 2SA1306B

DESCRIPTION

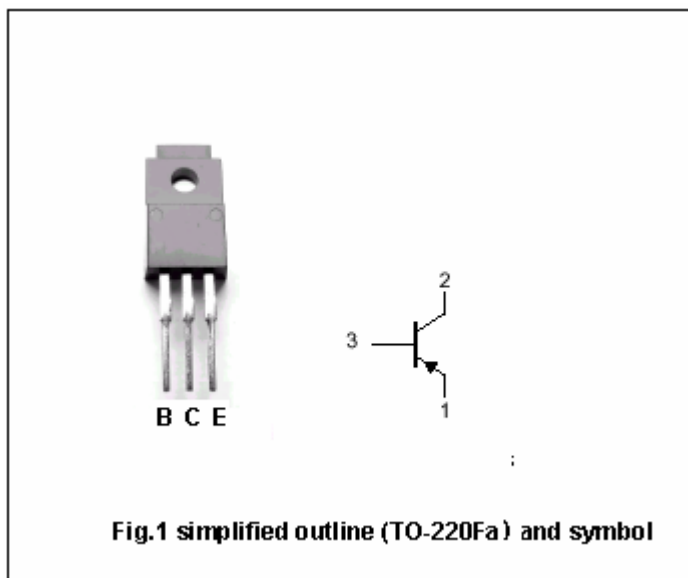
- With TO-220Fa package
- Complement to type
2SC3298,2SC3298A,2SC3298B

APPLICATIONS

- Power amplifier applications
- Driver stage amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SA1306	-160	V
		2SA1306A	-180	
		2SA1306B	-200	
V _{CEO}	Collector-emitter voltage	2SA1306	-160	V
		2SA1306A	-180	
		2SA1306B	-200	
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-1.5	A
I _B	Base current		-0.15	A
P _C	Collector power dissipation	T _C =25°C	20	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

Silicon PNP Power Transistors

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SA1306	-160			V
		2SA1306A	-180			
		2SA1306B	-200			
V _{CEsat}	Collector-emitter saturation voltage	I _C =-0.5A, I _B =-50mA			-1.5	V
V _{BE}	Base-emitter voltage	I _C =-0.5A, V _{CE} =-5V			-1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-160V, I _E =0			-1.0	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V, I _C =0			-1.0	μA
h _{FE}	DC current gain	I _C =-0.1A; V _{CE} =-5V	70		240	
C _{ob}	Output capacitance	I _E =0; V _{CB} =-10V, f=1MHz		30		pF
f _T	Transition frequency	I _C =-0.1A; V _{CE} =-10V		100		MHz

◆ h_{FE} Classifications

O	Y
70-140	120-240

PACKAGE OUTLINE

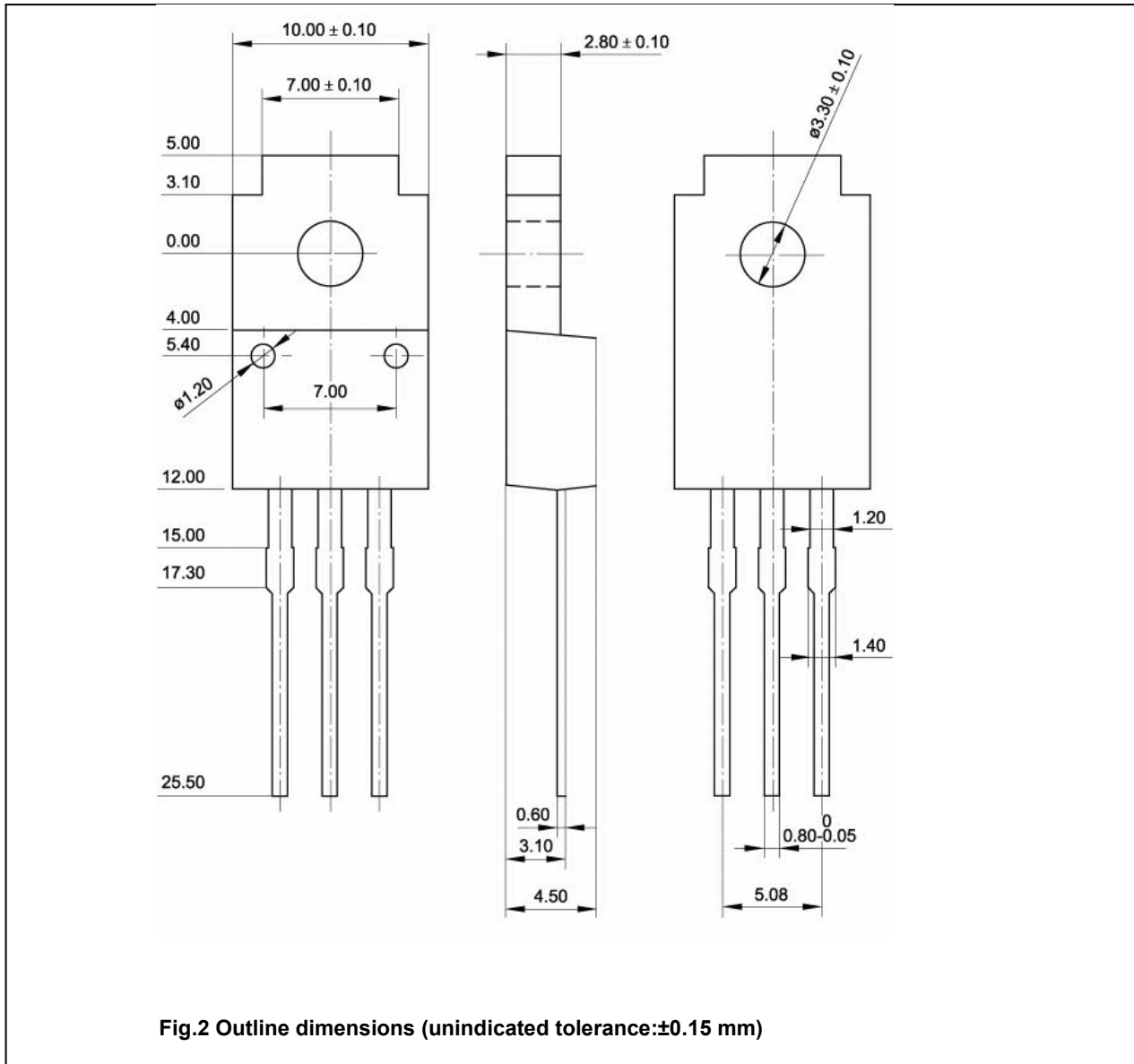


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)